

10/066,645

L Number	Hits	Search Text	DB	Time stamp
-	2732	silk and dielectric and @ad<20020206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 17:36
-	288	(silk near5 dielectric) and @ad<20020206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:21
-	288	(silk near5 dielectric) and @ad<20020206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:24
-	103	((silk near5 dielectric) and @ad<20020206 ) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:24
-	26	((((silk near5 dielectric) and @ad<20020206 ) and wafer) and bond\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 15:46
-	4	((silk near5 dielectric) and @ad<20020206 ) and (wafer near5 bond\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:01
-	592	(438/455).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:02
-	526	((438/455).CCLS.) and @ad<20020206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:02
-	3	((((438/455).CCLS.) and @ad<20020206) and (ild (interlevel adj dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:04
-	3	((((438/455).CCLS.) and @ad<20020206) and silk	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:06
-	201	((((438/455).CCLS.) and @ad<20020206) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:23
-	3868	(wafer adj bond\$) and @ad<20020206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:29

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-	1345	((wafer adj bond\$) and @ad<20020206) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:29
-	754	((((wafer adj bond\$) and @ad<20020206) and dielectric) and (cmp polish\$ grind\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:30
-	689	(((((wafer adj bond\$) and @ad<20020206) and dielectric) and (cmp polish\$ grind\$)) and etch\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:45
-	6	(((((wafer adj bond\$) and @ad<20020206) and dielectric) and (cmp polish\$ grind\$)) and etch\$) and silk	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:35
-	689	(((((wafer adj bond\$) and @ad<20020206) and dielectric) and (cmp polish\$ grind\$)) and etch\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 16:46
-	2	("5515604").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 20:32
-	1480	(438/692).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 20:33
-	1408	((438/692).CCLS.) and @ad<20020206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 20:33
-	823	((((438/692).CCLS.) and @ad<20020206) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 20:33
-	398	(((((438/692).CCLS.) and @ad<20020206) and dielectric) and (copper cu)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 20:34
-	40	(((((438/692).CCLS.) and @ad<20020206) and dielectric) and (copper cu)) and (faster adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 21:39
-	8	("4789648") or ("4671851") or ("4910155") or ("4944836")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 21:39